

## R-C Thermal Model Parameters

### DESCRIPTION

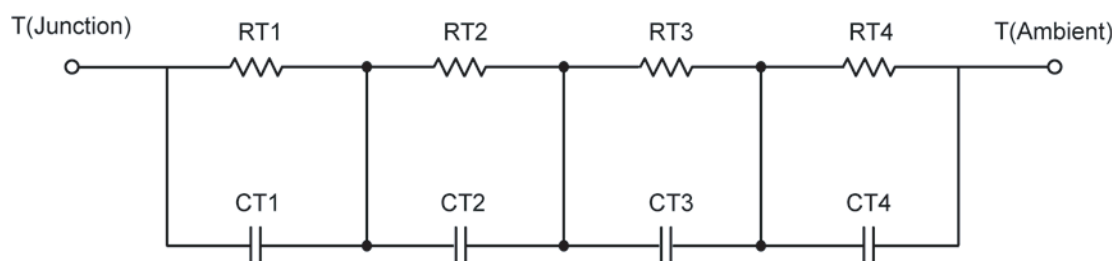
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

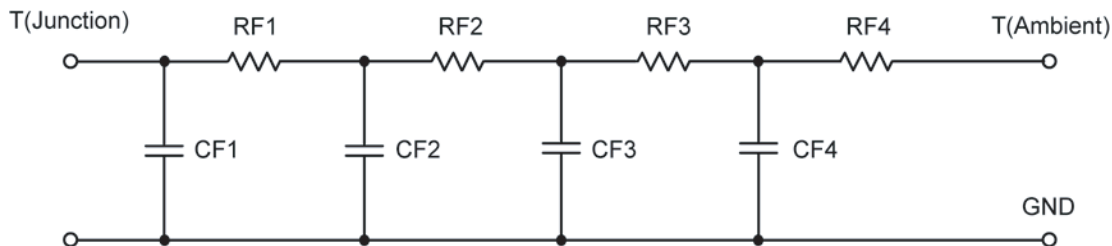
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance ( $^{\circ}\text{C/W}$ )			
Junction to	Ambient	Case	Foot
RT1	16.6549	N/A	11.1439
RT2	11.1784	N/A	5.1974
RT3	28.9565	N/A	3.0531
RT4	52.4564	N/A	17.3792
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CT1	98.6805 m	N/A	18.4700 m
CT2	501.5862 $\mu$	N/A	397.5663 $\mu$
CT3	5.9362 m	N/A	1.5350
CT4	1.4829	N/A	3.1863 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION**

<b>R-C VALUES FOR FILTER CONFIGURATION</b>			
<b>Thermal Resistance (°C/W)</b>			
<b>Junction to</b>	<b>Ambient</b>	<b>Case</b>	<b>Foot</b>
RF1	12.9729	N/A	6.7320
RF2	24.2701	N/A	11.7053
RF3	19.7308	N/A	11.4814
RF4	52.1097	N/A	5.5627
<b>Thermal Capacitance (Joules/°C)</b>			
<b>Junction to</b>	<b>Ambient</b>	<b>Case</b>	<b>Foot</b>
CF1	479.1678 $\mu$	N/A	377.2233 $\mu$
CF2	4.3538 m	N/A	2.0619 m
CF3	37.4663 m	N/A	2.1553 m
CF4	1.3900	N/A	69.7905 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

